

SUBSTRATE PROPERTY	MGSi8NTDNaS	MGSi8NTDNSb	MGSi8NTDNP	MGSi8NTDPB
Diameter	200 mm			
Growth Method	NTD			
Orientation	<100>, <110>, <111>			
Carrier Type	N-type			P-type
Dopant	As	Sb	P	B
Resistivity	30-600 $\Omega \cdot \text{cm}$			
Thickness	725 $\mu\text{m} \pm 25 \mu\text{m}$			
TTV	$\leq 10 \mu\text{m}$			
Bow	$\leq 60 \mu\text{m}$			

*The other specifications can be customized according to customer's requirements